

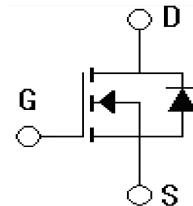
## Features

- Low gate charge(typ.Q<sub>g</sub>=46nC)
- Ultra fast switching
- 100% avalanche tested
- RoHS Compliant



## Applications

- Power factor correction(PFC).
- Switched mode power supplies(SMPS).
- Uninterrupted Power Supply(UPS).
- Low Power chargers and Adapters



## Absolute Ratings (T<sub>c</sub>=25°C)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	800	V
Drain Current -continuous	I <sub>D</sub>	24	A
Drain Current - pulse (note 1)	I <sub>DM</sub>	96	A
Gate-Source Voltage	V <sub>GSS</sub>	±30	V
Single Pulsed Avalanche Energy (note 2)	E <sub>AS</sub>	690	mJ
Power Dissipation	PD TC=25°C -Derate above 25°C	208	W
		1.67	W/°C
Operating and Storage Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-55~+150	°C
Continuous diode forward current	I <sub>S</sub>	24	A
Diode pulse current	I <sub>S</sub> Pulse	96	A
Maximum lead temperature for soldering purposes	T <sub>L</sub>	260	°C

\*Drain current limited by maximum junction temperature

**Electrical Characteristics**( $T_{CASE}=25^{\circ}\text{C}$  unless otherwise specified)

Parameter	Symbol	Tests conditions	Min	Type	Max	Units
<b>Off-Characteristics</b>						
Drain-Source Voltage	$\text{BV}_{\text{DSS}}$	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	800	-	-	V
Breakdown Voltage Temperature Coefficient	$\Delta \text{BV}_{\text{DSS}} / \Delta T_J$	$I_D=250\mu\text{A}$ , referenced to $25^{\circ}\text{C}$	-	0.11	-	V/ $^{\circ}\text{C}$
Drain cut-off current	$I_{\text{DSS}}$	$V_{DS}=800\text{V}, V_{GS}=0\text{V}$ $T_J=25^{\circ}\text{C}$	-	-	1	$\mu\text{A}$
		$T_J=150^{\circ}\text{C}$	-	-	100	
Gate-body leakage current,forward	$I_{GSSF}$	$V_{DS}=0\text{V}, V_{GS}=30\text{V}$	-	-	100	nA
Gate-body leakage current,reverse	$I_{GSSR}$	$V_{DS}=0\text{V}, V_{GS}=-30\text{V}$	-100	-	-	nA
<b>On-Characteristics</b>						
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	2.5	-	4.5	V
Static Drain-Source On-Resistance	$R_{DS(\text{ON})}$	$V_{GS}=10\text{V}, I_D=12\text{A}$ $T_J=25^{\circ}\text{C}$	-	0.205	0.24	$\Omega$
<b>Dynamic Characteristics</b>						
Input capacitance	$C_{iss}$	$V_{DS}=100\text{V},$ $V_{GS}=0\text{V},$ $f=10\text{kHz}$	-	2030	-	pF
Output capacitance	$C_{oss}$		-	83	-	pF
Reverse transfer capacitance	$C_{rss}$		-	1.8	-	pF

<b>Switching Characteristics</b>						
Turn-On delay time	$t_{d(on)}$	$V_{DD}=400\text{V}, I_D=24\text{A},$ $R_G=4.7\Omega$	-	20	-	ns
Turn-On rise time	$t_r$		-	39	-	ns
Turn-Off delay time	$T_{d(off)}$		-	56	-	ns
Turn-Off Fall time	$t_f$		-	19	-	ns
Total Gate Charge	$Q_g$	$V_{DD}=400\text{V},$ $I_D=24\text{A},$ $V_{GS}=10\text{V}$	-	46	-	nC
Gate-Source charge	$Q_{gs}$		-	13	-	nC
Gate-Drain charge	$Q_{gd}$		-	21	-	nC

<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
Drain-Source Diode Forward Voltage	$V_{SD}$	$V_{GS}=0\text{V}, IF=24\text{A}$ (note 3)	-	0.9	1.4	V
Reverse recovery time	$trr$	$VR=400\text{V}, IF=12\text{A}$	-	280	-	ns

Reverse recovery charge	Qrr	$dI/dt=130A/\mu s$	-	4.8	-	uC
Peak reverse recovery current	I <sub>rrm</sub>		-	24	-	A

## Thermal Characteristic

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R <sub>θJC</sub>	0.55	°C/W
Thermal Resistance, Junction-to-Ambient	R <sub>θJA</sub>	62.5	°C/W

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. ID = 10A, VDD = 50V, RG = 25Ω, Starting TJ = 25°C
3. Identical low side and high side switch with identical RG

## Electrical Characteristics

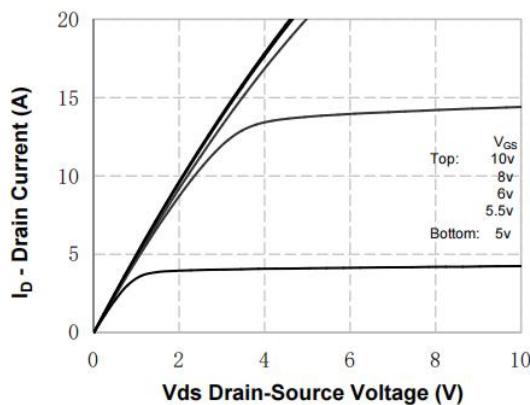


Figure 1. On-Region Characteristics

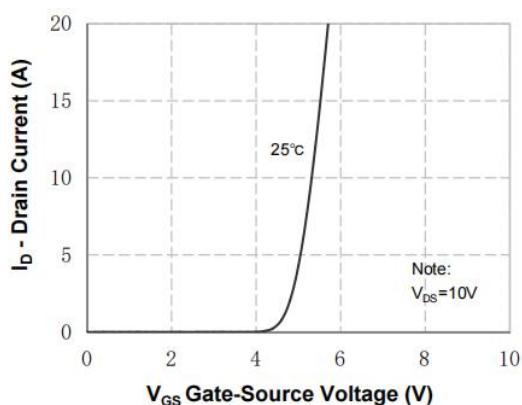


Figure 2. Transfer Characteristics

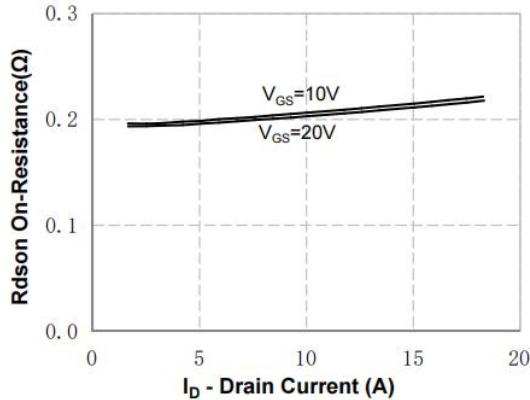


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

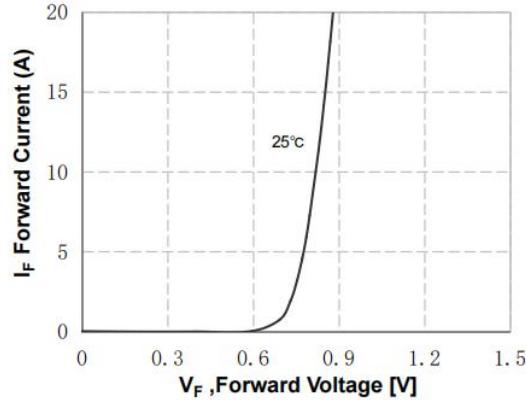
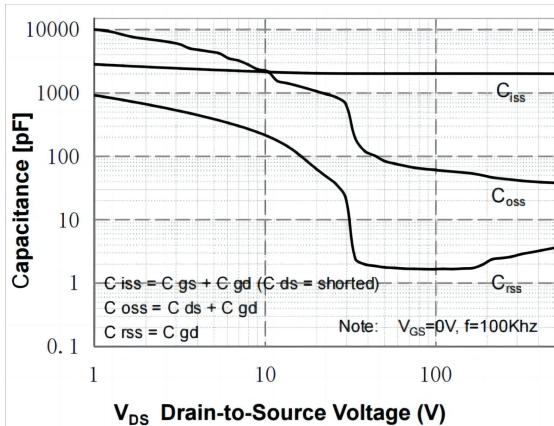
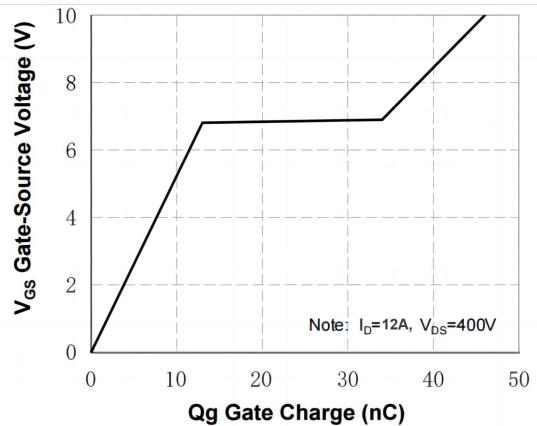
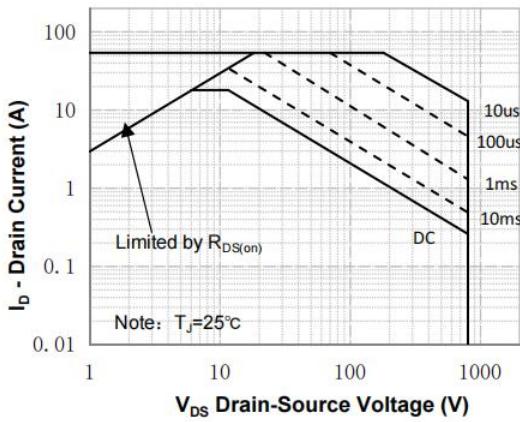
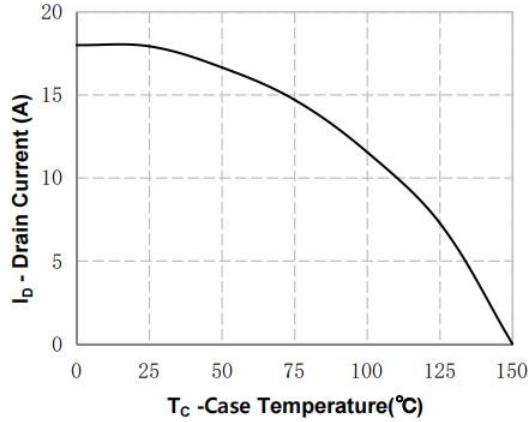
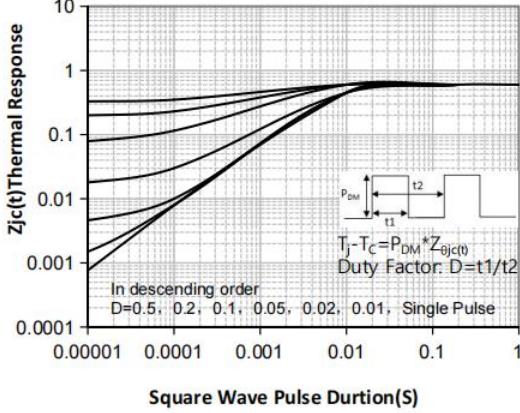
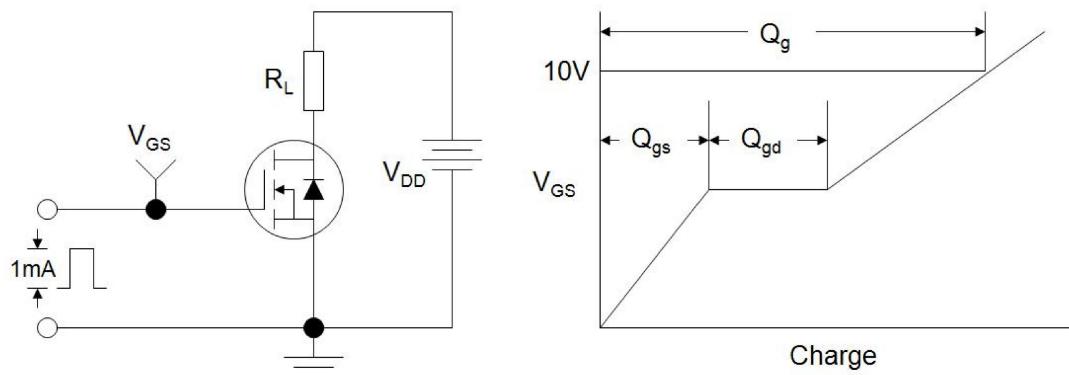
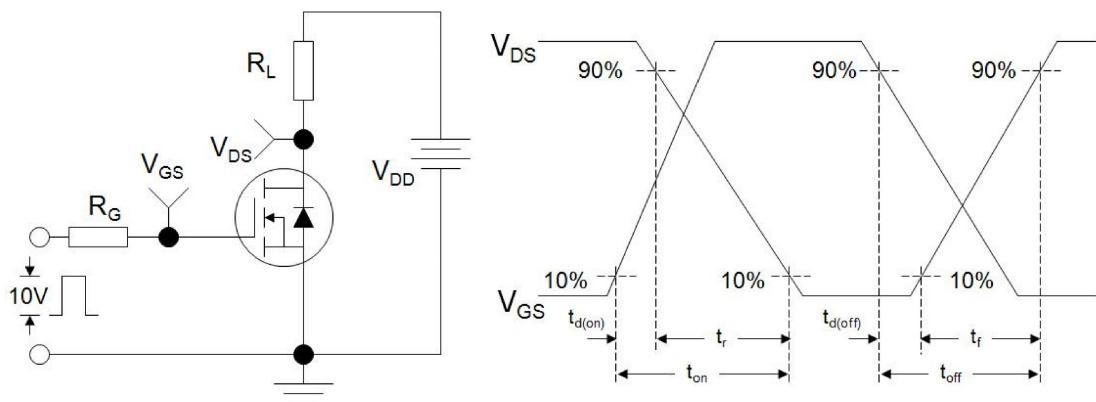
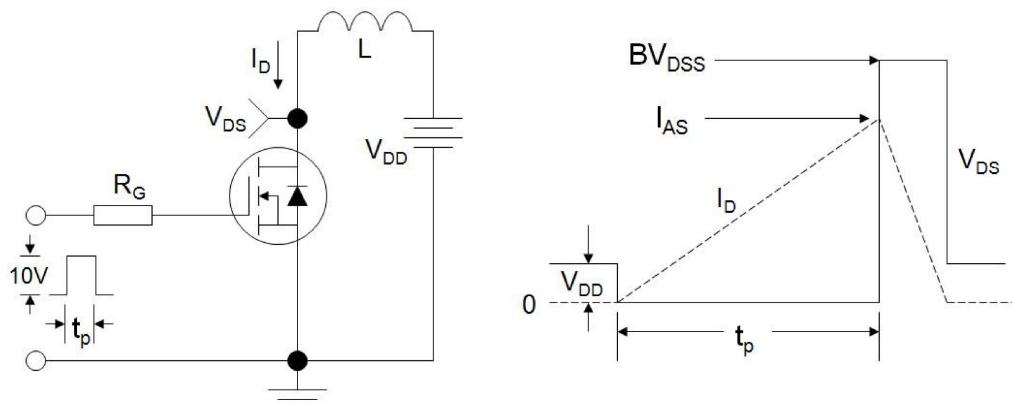
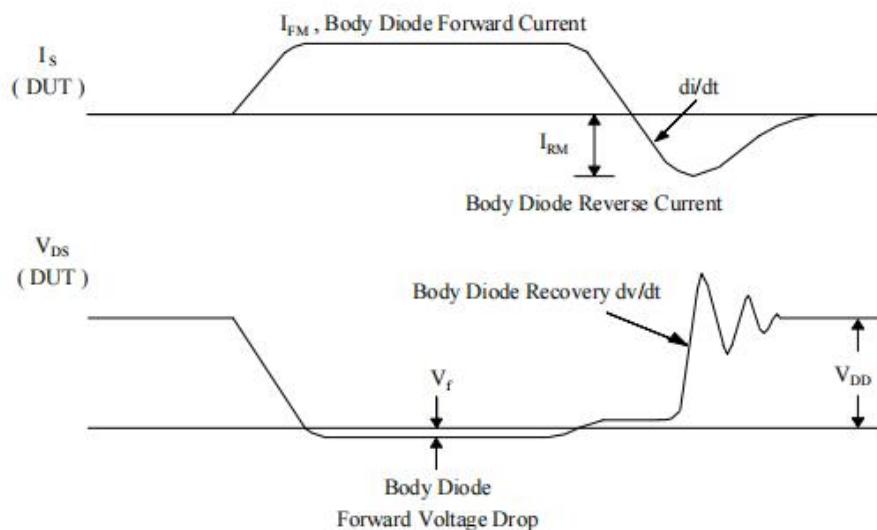
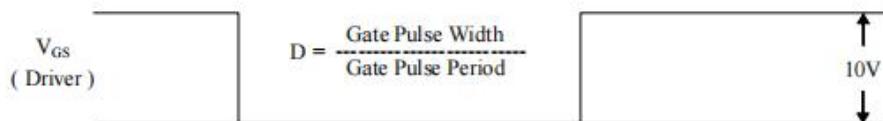
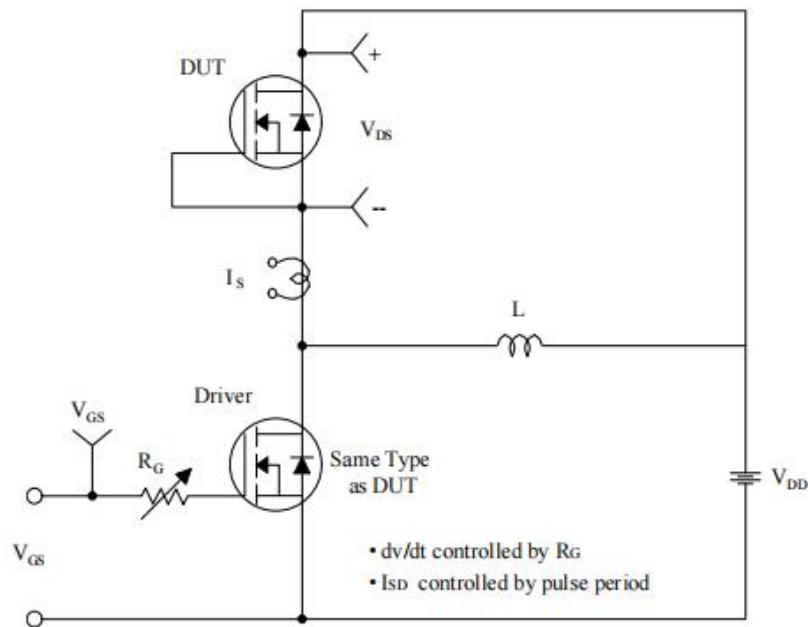


Figure 4. Body Diode Forward Voltage Variation with Source Current


**Figure 5. Capacitance Characteristics**

**Figure 6. Gate Charge Characteristics**

**Figure 7. Maximum Safe Operating Area**

**Figure 8. Maximum Drain Current vs Case Temperature**

**Figure 9. Transient Thermal Response Curve**

**Gate Charge Test Circuit and Waveform**

**Resistive Switching Test Circuit and Waveform**

**Unclamped Inductive Switching Test Circuit and Waveform**


### Peak Diode Recovery dv/dt Test Circuit & Waveforms



## Package Mechanical DATA

